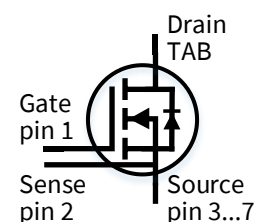


IMBG120R350M1H

CoolSiC™ 1200V SiC Trench MOSFET with .XT interconnection technology

Features

- Very low switching losses
- Short circuit withstand time 3 μ s
- Fully controllable dV/dt
- Benchmark gate threshold voltage, $V_{GS(th)} = 4.5V$
- Robust against parasitic turn on, 0V turn-off gate voltage can be applied
- Robust body diode for hard commutation
- .XT interconnection technology for best-in-class thermal performance
- Package creepage and clearance distance > 6.1mm
- Sense pin for optimized switching performance



Benefits

- Efficiency improvement
- Enabling higher frequency
- Increased power density
- Cooling effort reduction
- Reduction of system complexity and cost



Potential applications

- Drives
- Infrastructure – Charger
- Energy generation - Solar string inverter and solar optimizer
- Industrial power supplies - Industrial UPS



Product validation

Qualified for industrial applications according to the relevant tests of JEDEC 47/20/22

Note: the source and sense pins are not exchangeable, their exchange might lead to malfunction

Table 1 Key Performance and Package Parameters

Type	V_{DS}	I_D $T_C = 25^\circ C, R_{th(j-c, max)}$	$R_{DS(on)}$ $T_{vj} = 25^\circ C, I_D = 2A, V_{GS} = 18V$	$T_{vj, max}$	Marking	Package
IMBG120R350M1H	1200V	4.7A	350m Ω	175 $^\circ C$	12M1H350	PG-TO263-7

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Maximum ratings

1 Maximum ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Table 2 Maximum ratings

Parameter	Symbol	Value	Unit
Drain-source voltage, $T_{vj} \geq 25^{\circ}\text{C}$	V_{DSS}	1200	V
DC drain current for $R_{th(j-c,max)}$, limited by T_{vjmax} , $V_{GS} = 18\text{V}$, $T_C = 25^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$	I_D	4.7 4.7	A
Pulsed drain current, t_p limited by T_{vjmax} , $V_{GS} = 18\text{V}$	$I_{D,pulse}^1$	17	A
DC body diode forward current for $R_{th(j-c,max)}$, limited by T_{vjmax} , $V_{GS} = 0\text{V}$ $T_C = 25^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$	I_{SD}	4.7 4.7	A
Pulsed body diode current, t_p limited by T_{vjmax}	$I_{SD,pulse}^1$	17	A
Gate-source voltage ² Max transient voltage, < 1% duty cycle Recommended turn-on gate voltage Recommended turn-off gate voltage	V_{GS} $V_{GS,on}$ $V_{GS,off}$	-7... 23 15... 18 0	V
Short-circuit withstand time $V_{DD} = 800\text{V}$, $V_{DS,peak} < 1200\text{V}$, $V_{GS,on} = 15\text{V}$, $T_{j,start} = 25^{\circ}\text{C}$	t_{SC}	3	μs
Power dissipation, limited by T_{vjmax} $T_C = 25^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$	P_{tot}	65 33	W
Virtual junction temperature	T_{vj}	-55... 175	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55... 150	$^{\circ}\text{C}$
Soldering temperature Reflow soldering (MSL1 according to JEDEC J-STD-020)	T_{sold}	260	$^{\circ}\text{C}$

¹ verified by design

² **Important note:** The selection of positive and negative gate-source voltages impacts the long-term behavior of the device. The design guidelines described in [Application Note AN2018-09](#) must be considered to ensure sound operation of the device over the planned lifetime.

2 Thermal resistances

Table 3

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
MOSFET/body diode thermal resistance, junction – case	$R_{th(j-c)}$		-	1.8	2.3	K/W
Thermal resistance, junction – ambient	$R_{th(j-a)}$	leaded	-	-	62	K/W

3 Electrical Characteristics

3.1 Static characteristics

Table 4 Static characteristics (at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 18\text{V}, I_D = 2\text{A},$ $T_{vj} = 25^{\circ}\text{C}$	-	350	468	mΩ
		$T_{vj} = 100^{\circ}\text{C}$	-	446	-	
		$T_{vj} = 175^{\circ}\text{C}$	-	662	-	
		$V_{GS} = 15\text{V}, I_D = 2\text{A},$ $T_{vj} = 25^{\circ}\text{C}$	-	450	598	
Body diode forward voltage	V_{SD}	$V_{GS} = 0\text{V}, I_{SD} = 2\text{A}$ $T_{vj} = 25^{\circ}\text{C}$	-	4.1	5.2	V
		$T_{vj} = 100^{\circ}\text{C}$	-	4.0	-	
		$T_{vj} = 175^{\circ}\text{C}$	-	3.9	-	
Gate-source threshold voltage	$V_{GS(th)}$	(tested after 1 ms pulse at $V_{GS} = 20\text{V}$) $I_D = 1\text{mA}, V_{DS} = V_{GS}$ $T_{vj} = 25^{\circ}\text{C}$	3.5	4.5	5.7	V
		$T_{vj} = 175^{\circ}\text{C}$	-	3.6	-	
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0\text{V}, V_{DS} = 1200\text{V}$ $T_{vj} = 25^{\circ}\text{C}$	-	0.1	20	μA
		$T_{vj} = 175^{\circ}\text{C}$	-	0.3	-	
Gate-source leakage current	I_{GSS}	$V_{GS} = 23\text{V}, V_{DS} = 0\text{V}$	-	-	100	nA
		$V_{GS} = -7\text{V}, V_{DS} = 0\text{V}$	-	-	-100	nA
Transconductance	g_{fs}	$V_{DS} = 20\text{V}, I_D = 2\text{A}$	-	1.2	-	S
Internal gate resistance	$R_{G,int}$	$f = 1\text{MHz}, V_{AC} = 25\text{mV}$	-	35	-	Ω

3.2 Dynamic characteristics

Table 5 Dynamic characteristics (at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	C_{iss}	$V_{DD} = 800\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}, V_{AC} = 25\text{mV}$	-	196	-	pF
Output capacitance	C_{oss}		-	9	-	
Reverse capacitance	C_{rss}		-	0.94	-	
C_{oss} stored energy	E_{oss}		-	3.8	-	μJ
Total gate charge	Q_G	$V_{DD} = 800\text{V}, I_D = 2\text{A},$ $V_{GS} = 0/18\text{V}, \text{turn-on pulse}$	-	5.9	-	nC
Gate to source charge	$Q_{GS,pl}$		-	1.5	-	
Gate to drain charge	Q_{GD}		-	1.2	-	

3.3 Switching characteristics

Table 6 Switching characteristics, Inductive load ³

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
MOSFET Characteristics, $T_{vj} = 25^{\circ}\text{C}$						
Turn-on delay time	$t_{d(\text{on})}$	$V_{DD} = 800\text{V}$, $I_D = 2\text{A}$, $V_{GS} = 0/18\text{V}$, $R_{G,\text{ext}} = 2\Omega$, $L_{\sigma} = 40\text{nH}$, diode: body diode at $V_{GS} = 0\text{V}$ see Fig. E	-	6.3	-	ns
Rise time	t_r		-	0.7	-	
Turn-off delay time	$t_{d(\text{off})}$		-	17	-	
Fall time	t_f		-	16	-	
Turn-on energy	E_{on}		-	32	-	μJ
Turn-off energy	E_{off}		-	6.7	-	
Total switching energy	E_{tot}		-	39	-	
Body Diode Characteristics, $T_{vj} = 25^{\circ}\text{C}$						
Diode reverse recovery charge	Q_{rr}	$V_{DD} = 800\text{V}$, $I_{SD} = 2\text{A}$, V_{GS} at diode = 0V , $di_t/dt = 1000\text{A}/\mu\text{s}$, Q_{rr} includes also Q_C , see Fig. C	-	62	-	nC
Diode peak reverse recovery current	I_{rrm}		-	0.5	-	A
MOSFET Characteristics, $T_{vj} = 175^{\circ}\text{C}$						
Turn-on delay time	$t_{d(\text{on})}$	$V_{DD} = 800\text{V}$, $I_D = 2\text{A}$, $V_{GS} = 0/18\text{V}$, $R_{G,\text{ext}} = 2\Omega$, $L_{\sigma} = 40\text{nH}$, diode: body diode at $V_{GS} = 0\text{V}$ see Fig. E	-	6.3	-	ns
Rise time	t_r		-	1.7	-	
Turn-off delay time	$t_{d(\text{off})}$		-	17	-	
Fall time	t_f		-	16	-	
Turn-on energy	E_{on}		-	44	-	μJ
Turn-off energy	E_{off}		-	7.5	-	
Total switching energy	E_{tot}		-	51	-	
Body Diode Characteristics, $T_{vj} = 175^{\circ}\text{C}$						
Diode reverse recovery charge	Q_{rr}	$V_{DD} = 800\text{V}$, $I_{SD} = 2\text{A}$, V_{GS} at diode = 0V , $di_t/dt = 1000\text{A}/\mu\text{s}$, Q_{rr} includes also Q_C , see Fig. C	-	78	-	nC
Diode peak reverse recovery current	I_{rrm}		-	0.6	-	A

³ The chip technology was characterized up to $200\text{ kV}/\mu\text{s}$. The measured dV/dt was limited by measurement test setup and package.

4 Electrical characteristic diagrams

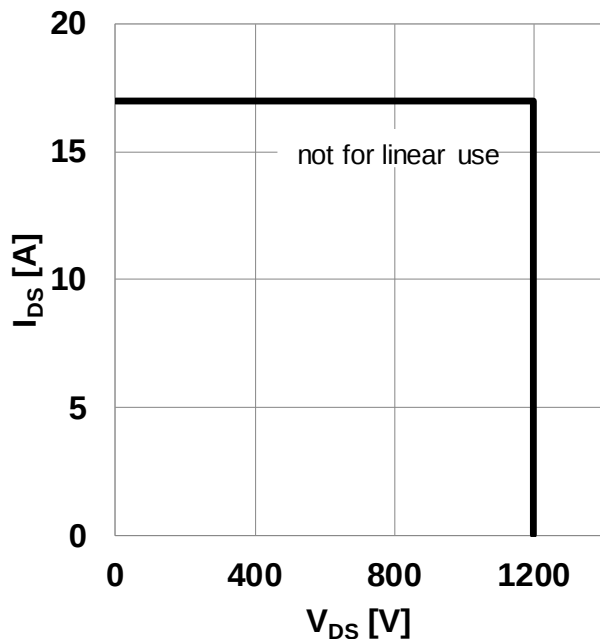


Figure 1 Safe operating area (SOA)
($V_{GS} = 0/18V$, $T_c = 25^\circ C$, $T_j \leq 175^\circ C$)

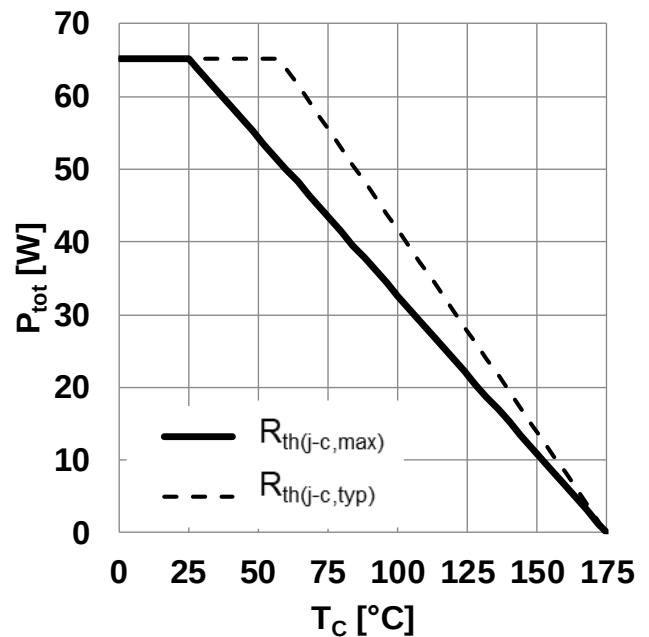


Figure 2 Power dissipation as a function of case temperature limited by bond wire
($P_{tot} = f(T_C)$)

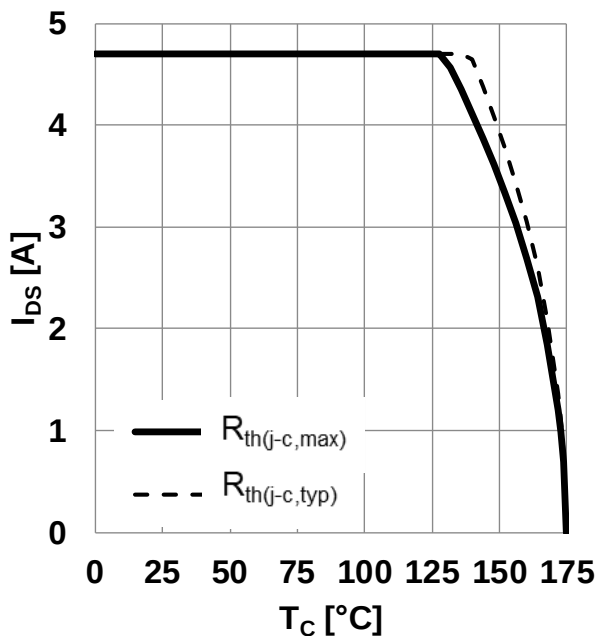


Figure 3 Maximum DC drain to source current as a function of case temperature limited by bond wire ($I_{DS} = f(T_C)$)

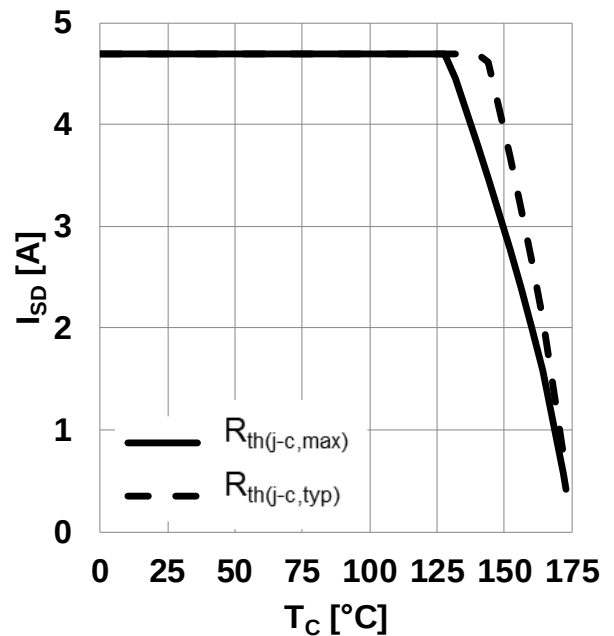


Figure 4 Maximum source to drain current as a function of case temperature limited by bond wire ($I_{SD} = f(T_C)$, $V_{GS} = 0V$)

Electrical characteristic diagrams

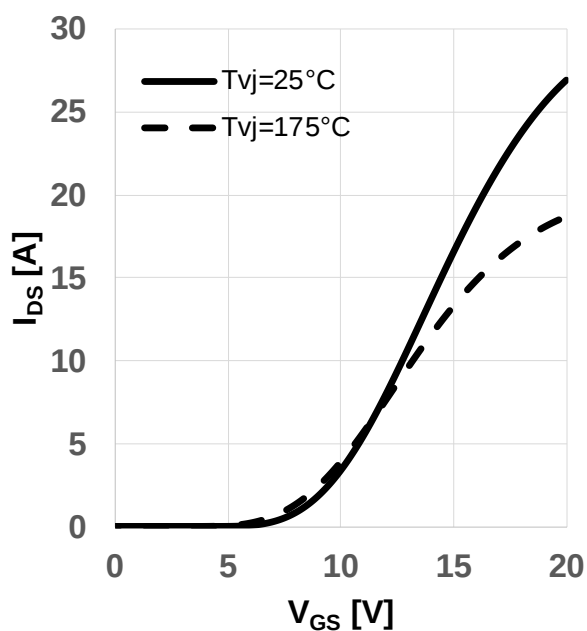


Figure 5 Typical transfer characteristic
($I_{DS} = f(V_{GS})$, $V_{DS} = 20V$, $t_P = 20\mu s$)

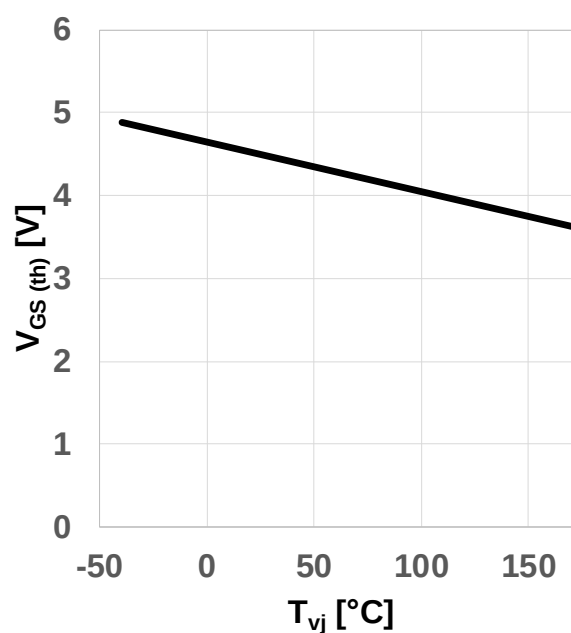


Figure 6 Typical gate-source threshold voltage
as a function of junction temperature
($V_{GS(th)} = f(T_{vj})$, $I_{DS} = 1mA$, $V_{GS} = V_{DS}$)

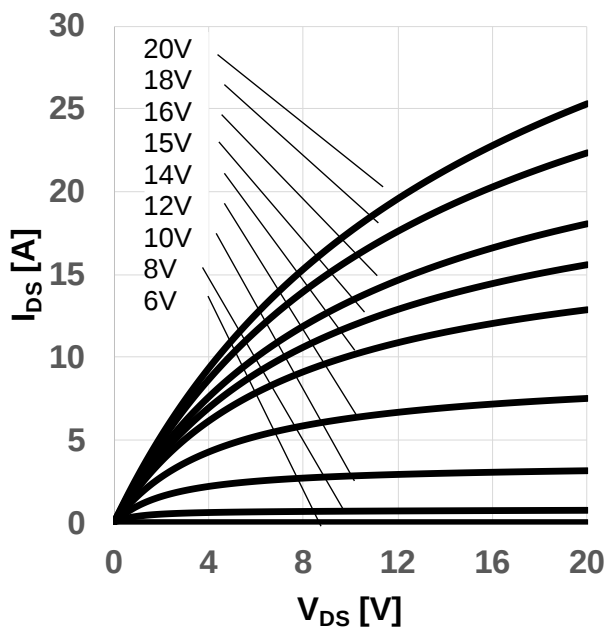


Figure 7 Typical output characteristic, V_{GS} as
parameter
($I_{DS} = f(V_{DS})$, $T_{vj} = 25^\circ C$, $t_P = 20\mu s$)

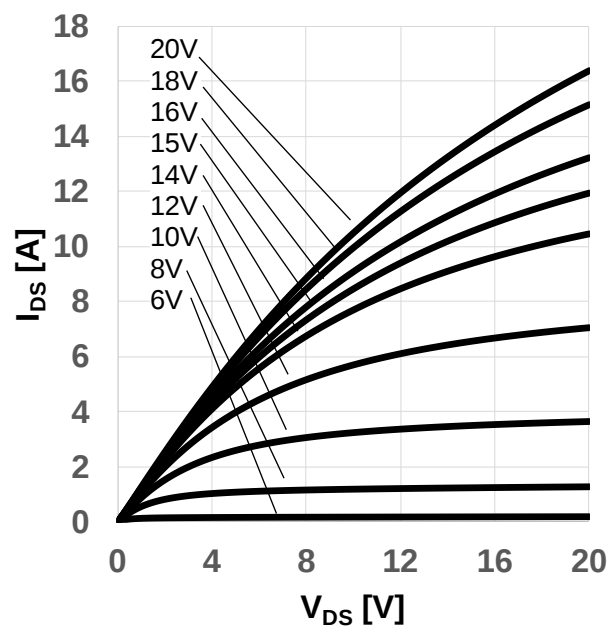


Figure 8 Typical output characteristic, V_{GS} as
parameter
($I_{DS} = f(V_{DS})$, $T_{vj} = 175^\circ C$, $t_P = 20\mu s$)

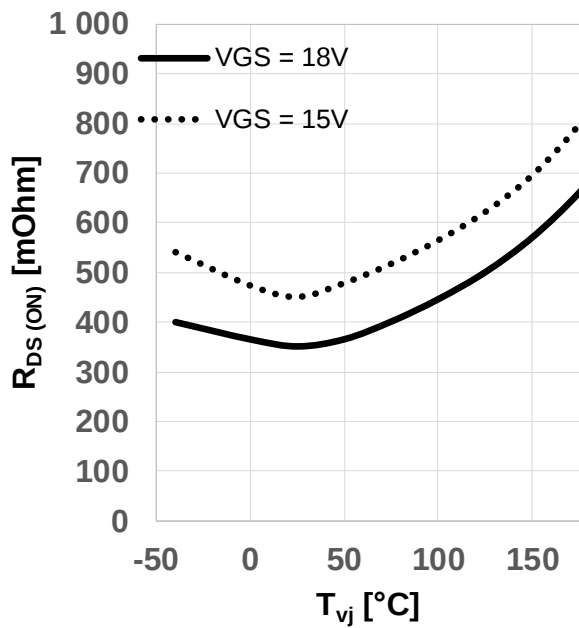


Figure 9 Typical on-resistance as a function of junction temperature
 $(R_{DS(on)} = f(T_{vj}), I_{DS} = 2A)$

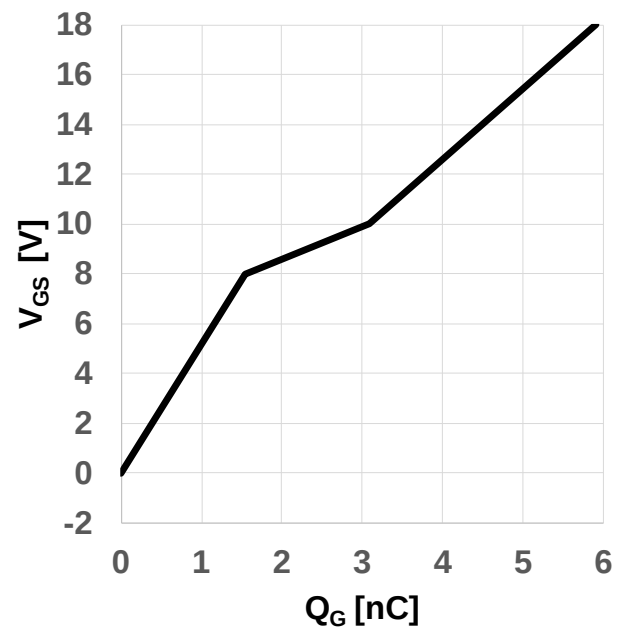


Figure 10 Typical gate charge
 $(V_{GS} = f(Q_G), I_{DS} = 2A, V_{DS} = 800V, \text{turn-on pulse})$

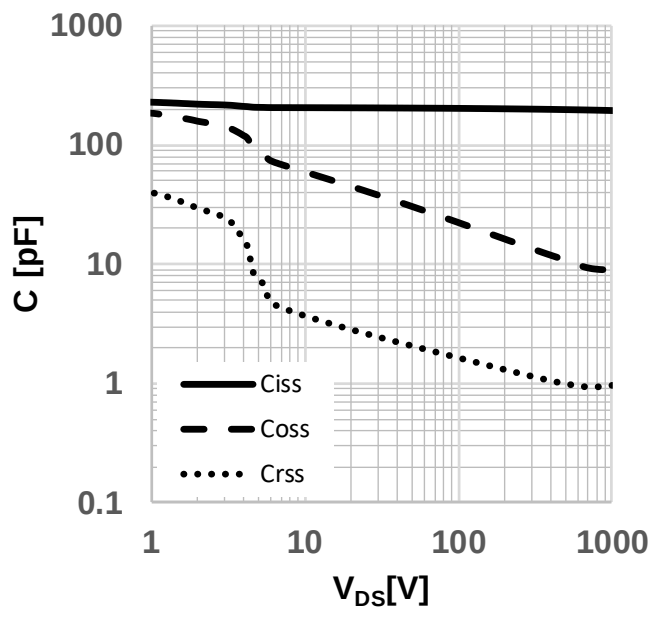


Figure 11 Typical capacitance as a function of drain-source voltage
 $(C = f(V_{DS}), V_{GS} = 0V, f = 1MHz)$

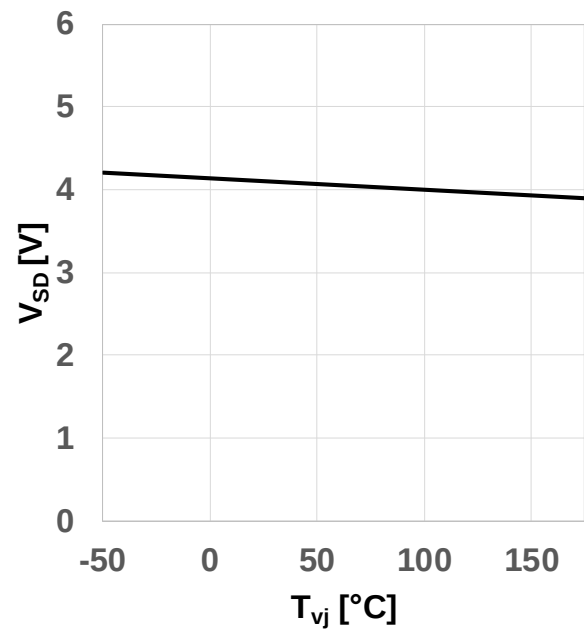


Figure 12 Typical body diode forward voltage as function of junction temperature
 $(V_{SD} = f(T_{vj}), V_{GS} = 0V, I_{SD} = 2A)$

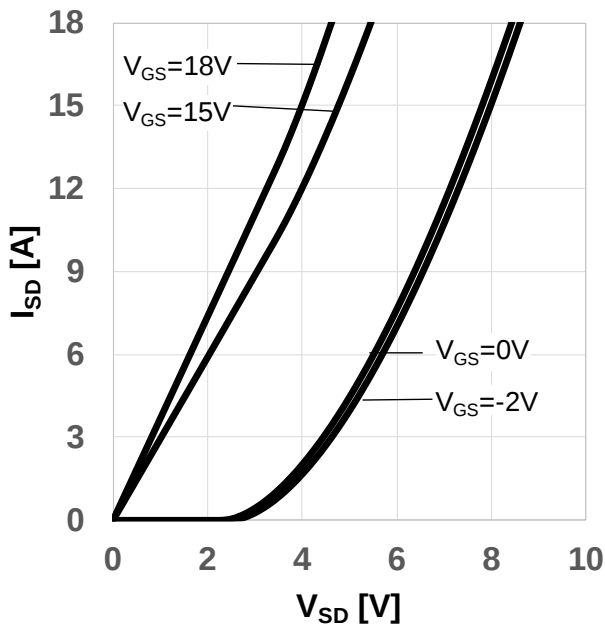


Figure 13 Typical body diode forward current as a function of forward voltage, V_{GS} as parameter

($I_{SD} = f(V_{SD})$, $T_{vj} = 25^\circ\text{C}$, $t_P = 20\mu\text{s}$)

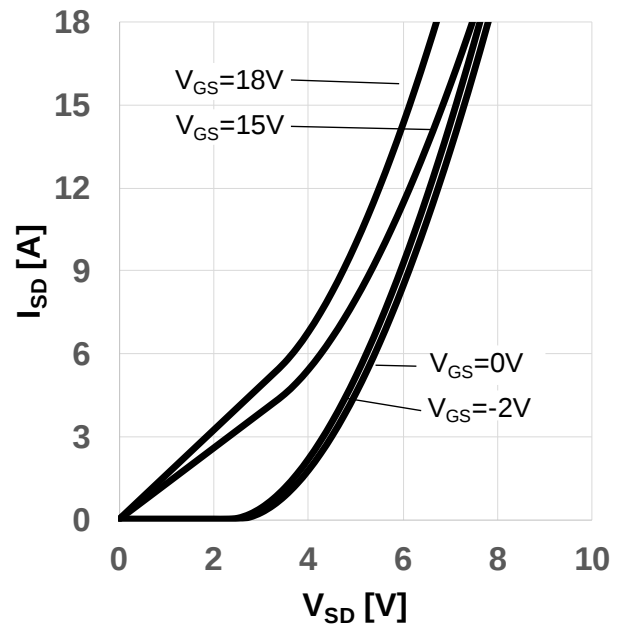


Figure 14 Typical body diode forward current as a function of forward voltage, V_{GS} as parameter

($I_{SD} = f(V_{SD})$, $T_{vj} = 175^\circ\text{C}$, $t_P = 20\mu\text{s}$)

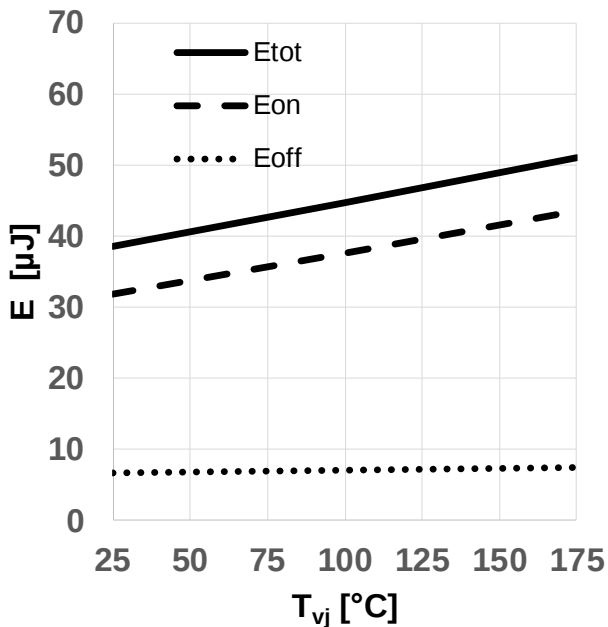


Figure 15 Typical switching energy losses as a function of junction temperature

($E = f(T_{vj})$, $V_{DD} = 800\text{V}$, $V_{GS} = 0\text{V}/18\text{V}$, $R_{G,ext} = 2\Omega$, $I_D = 2\text{A}$, ind. load, test circuit in Fig. E, diode: body diode at $V_{GS} = 0\text{V}$)

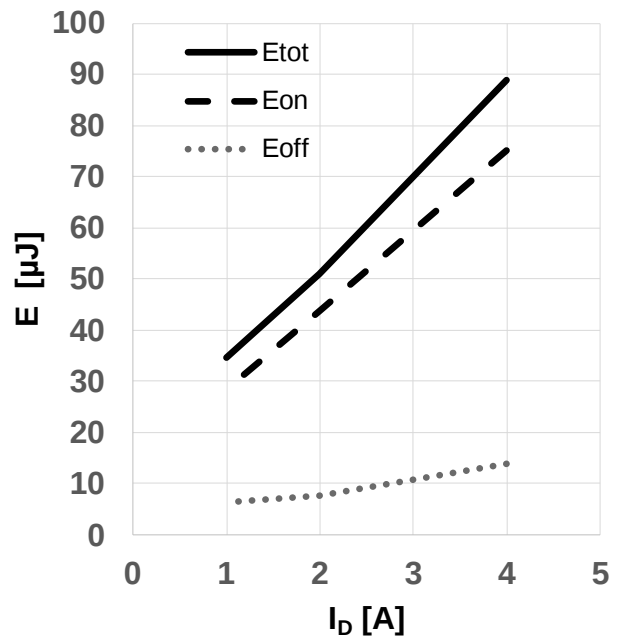


Figure 16 Typical switching energy losses as a function of drain-source current

($E = f(I_{DS})$, $V_{DD} = 800\text{V}$, $V_{GS} = 0\text{V}/18\text{V}$, $R_{G,ext} = 2\Omega$, $T_{vj} = 175^\circ\text{C}$, ind. load, test circuit in Fig. E, diode: body diode at $V_{GS} = 0\text{V}$)

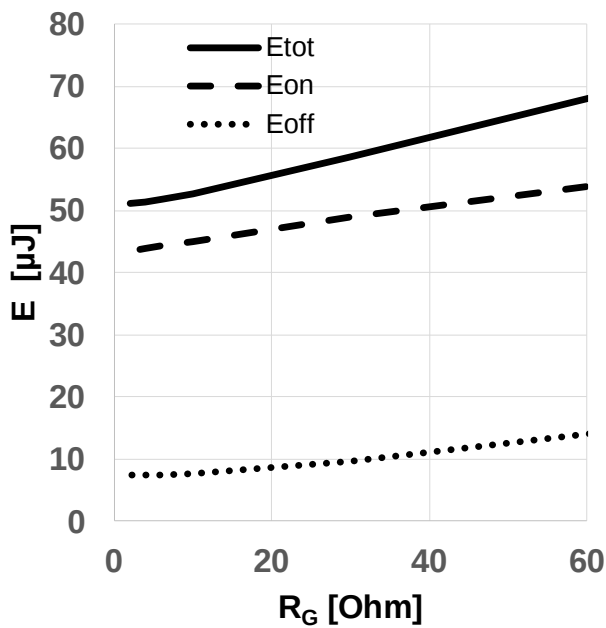


Figure 17 Typical switching energy losses as a function of gate resistance
 $(E = f(R_{G,ext}), V_{DD} = 800V, V_{GS} = 0V/18V, I_D = 2A, T_{vj} = 175^\circ C, \text{ind. load, test circuit in Fig. E, diode: body diode at } V_{GS} = 0V)$

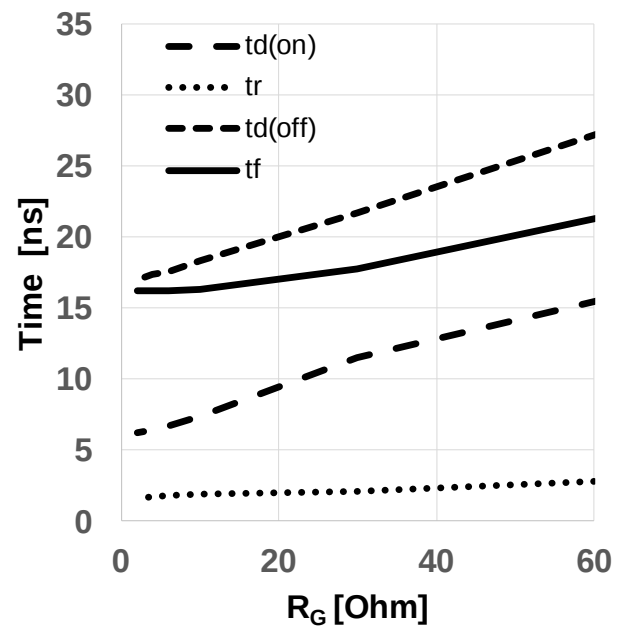


Figure 18 Typical switching times as a function of gate resistor
 $(t = f(R_{G,ext}), V_{DD} = 800V, V_{GS} = 0V/18V, I_D = 2A, T_{vj} = 175^\circ C, \text{ind. load, test circuit in Fig. E, diode: body diode at } V_{GS} = 0V)$

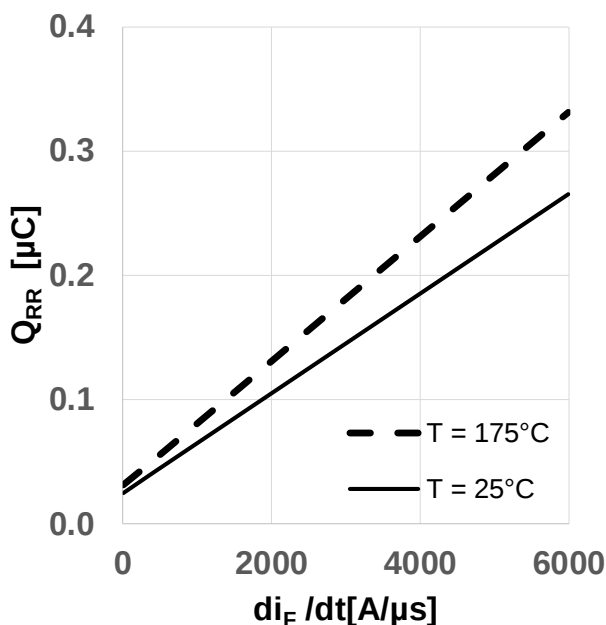


Figure 19 Typical reverse recovery charge as a function of diode current slope
 $(Q_{rr} = f(di_i/dt), V_{DD} = 800V, V_{GS} = 0V/18V, I_D = 2A, \text{ind. load, test circuit in Fig. E, body diode at } V_{GS} = 0V)$

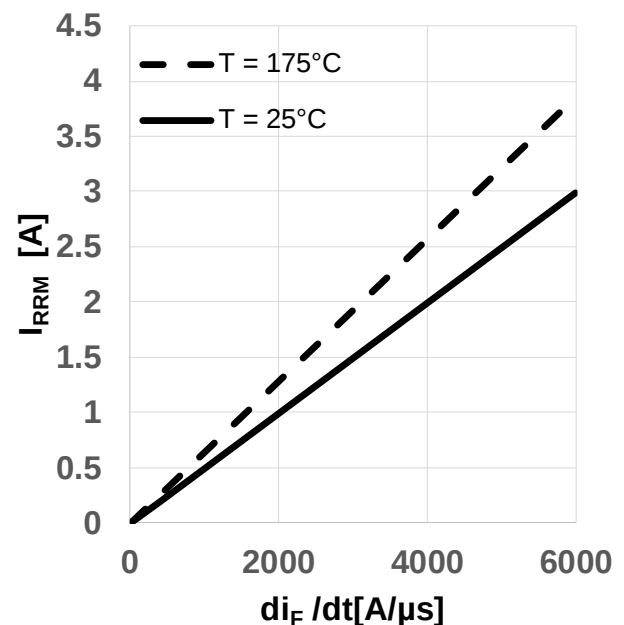


Figure 20 Typical reverse recovery current as a function of diode current slope
 $(I_{rrm} = f(di_i/dt), V_{DD} = 800V, V_{GS} = 0V/18V, I_D = 2A, \text{ind. load, test circuit in Fig. E, body diode at } V_{GS} = 0V)$

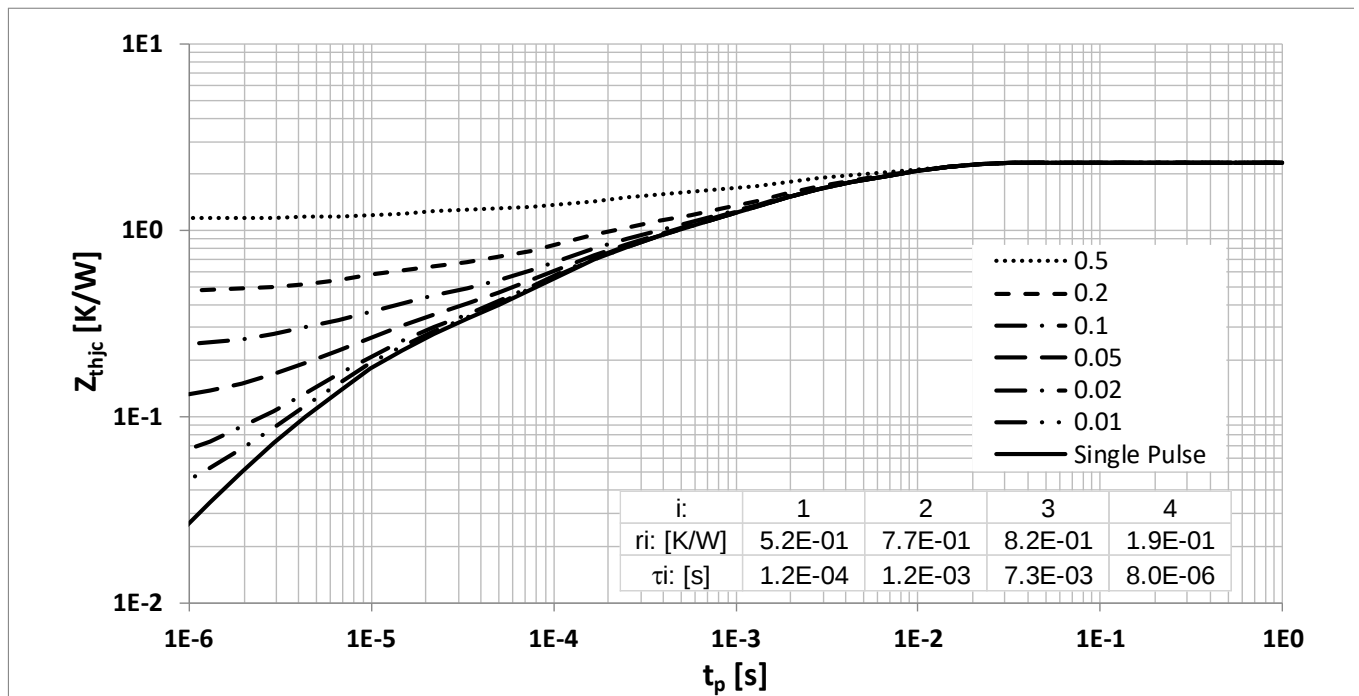


Figure 21 Max. transient thermal resistance (MOSFET/diode)

($Z_{th(j-c,max)} = f(t_p)$, parameter $D = t_p/T$, thermal equivalent circuit in Fig. D)

5 Package drawing

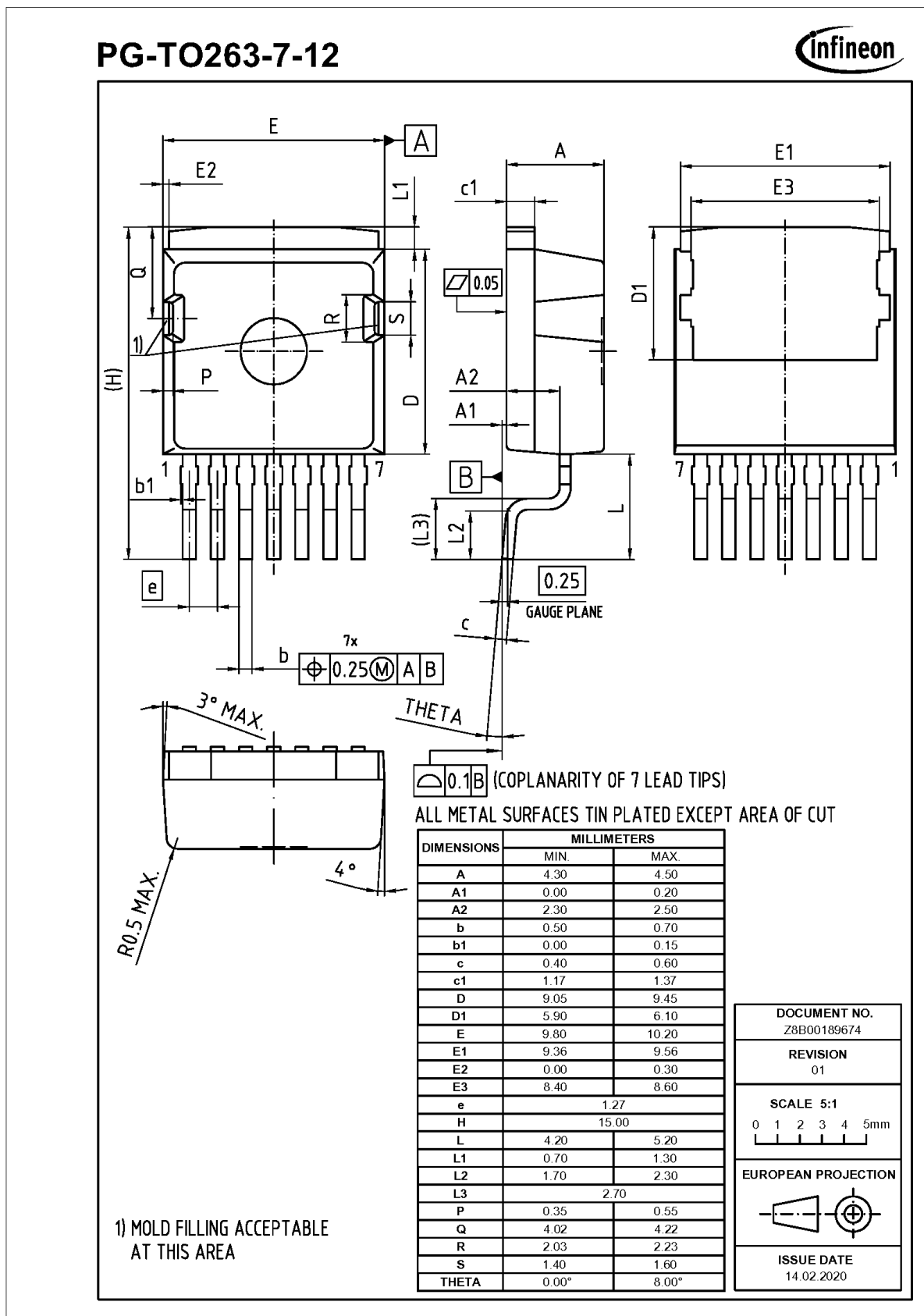


Figure 22 Package drawing

6 Test conditions

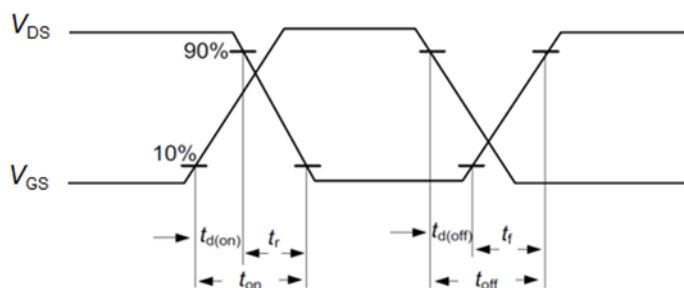


Figure A. Definition of switching times

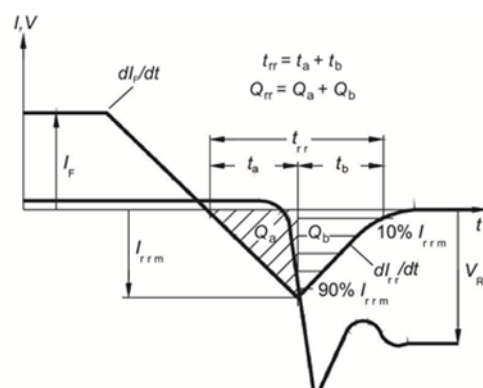


Figure C. Definition of diode switching characteristics

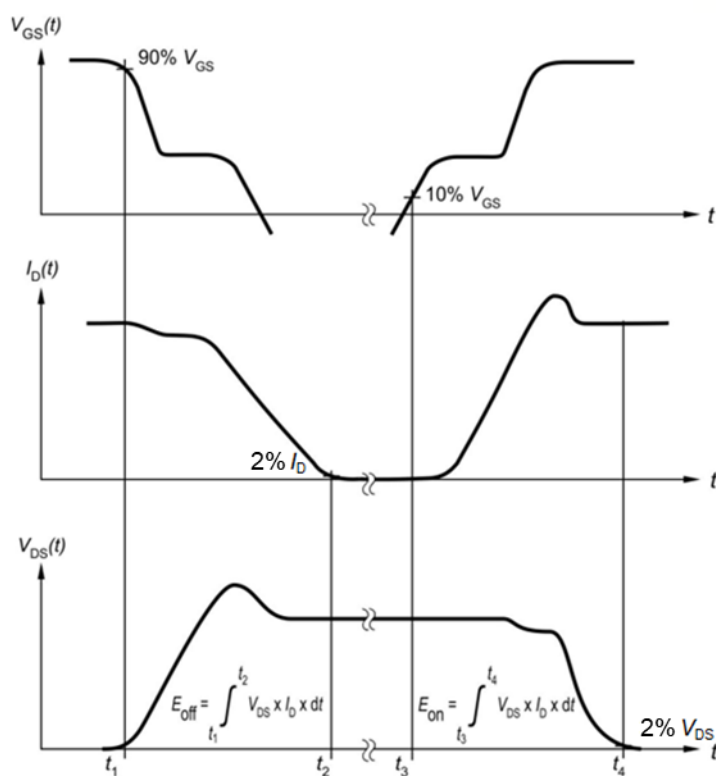


Figure B. Definition of switching losses

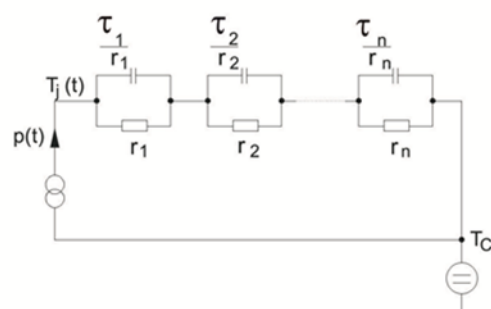


Figure D. Thermal equivalent circuit

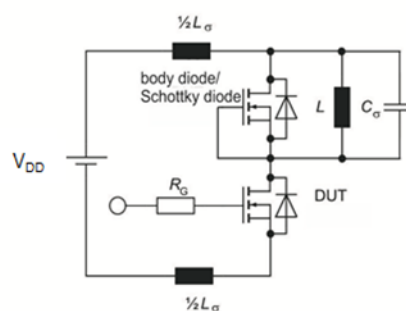


Figure E. Dynamic test circuit

Parasitic inductance L_{σ} ,
parasitic capacitor C_{σ} ,

Figure 23 Test conditions

Revision history

Revision history

Document version	Date of release	Description of changes
2.1	2020-09-01	Final Datasheet
2.2	2020-12-11	Correction of circuit symbol on page 1

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